mail

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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USB 2.0-Capable Ultra-Low THD DPDT Switch

The NL3S588 is a single supply, bidirectional, double-pole/ double-throw (DPDT) switch suitable for both hi-fidelity audio and high-speed data applications.

The NL3S588 features ultra-low distortion, high OFF–Isolation analog switches that can pass analog signals that are positive and negative with respect to ground. It is targeted at consumer and professional DC–coupled GND–referenced audio switching applications such as computer sound cards and home theater products.

The NL3S588 may also be used in high-speed differential data routing applications. Both channels are USB 2.0-compliant.

Features

- DPDT Switch
- 3.3 V Single Supply Operation
- Available in 1.4 mm x 1.8 mm UQFN10
- This Device is Pb–Free, Halogen Free/BFR Free and RoHS Compliant

Audio Capabilities

- 2 V_{RMS} Signal Switching
- -116 dB THD+N into 20 k Ω Load at 2 V_{RMS}
- -112 dB THD+N into 32Ω Load at 0.707 V_{RMS}
- Signal to Noise Ratio: > 125 dBV
- $\pm 0.004 \text{ dB}$ Insertion Loss at 1 kHz, 20 k Ω Load
- ±0.0008 dB Gain Variation 20 Hz to 20 kHz
- 112 dB Signal Muting into 20 k Ω Load
- 131 dB PSRR 20 Hz to 20 kHz

High-Speed Data Capabilities

- Input Signal Range: 0 V to V_{DD}
- C_{ON}: 8.9 pF (Typ)
- Data Rate: USB 2.0-Compliant up to 480 Mbps
- Bandwidth: 580 MHz

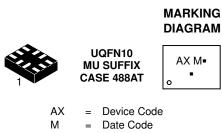
Applications

- Hi-Fi Audio Switching
- USB 2.0 High–Speed Data Switching
- USB 3.x Type C Switching



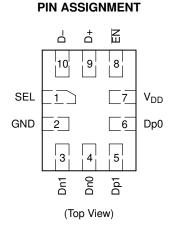
ON Semiconductor®

www.onsemi.com



= Pb–Free Device

(Note: Microdot may be in either location)



ORDERING INFORMATION

Device	Package	Shipping [†]
NL3S588MUTBG	UQFN10 (Pb-Free)	3000 / Tape & Reel

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

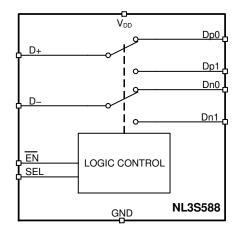


Figure 1. Block Diagram

FUNCTION TABLE

INP	UTS	
EN	SEL	Operating Mode
0	0	Dp0 connected to D+ / Dn0 connected to D-
0	1	Dp1 connected to D+ / Dn1 connected to D-
1	Х	Shutdown (I/Os Disconnected)

 $\begin{array}{ll} \mbox{NOTE:} & \overline{EN} \mbox{ Logic "0"} \leq 0.5 \mbox{ V, Logic "1"} \geq 1.4 \mbox{ V or float.} \\ & \mbox{SEL Logic "0"} \leq 0.5 \mbox{ V, Logic "1"} \geq 1.4 \mbox{ V.} \\ & \mbox{ X = Don't Care} \end{array}$

PIN DESCRIPTIONS

PIN NAME	PIN	DESCRIPTION
SEL	1	Channel Select
GND	2	Ground
Dn1	3	Normally–Open I/O
Dp1	5	
Dn0	4	Normally–Closed I/O
Dp0	6	
V _{DD}	7	System power supply pin (+3 V to +3.6 V)
EN	8	Signal mute control pin
D+	9	Common I/O
D-	10	

MAXIMUM RATINGS

Symbol	Rating		Value	Unit
V_{DD}	Positive 3 V DC Supply Voltage		-0.5 to +4.1	V
V _{IS}	Analog Input/Output Voltage (D+, D-, Dpx, Dnx)		-3.1 to V _{DD} + 0.5	V
V _{IN}	Digital Input Voltage (EN, SEL)		–0.5 to V _{DD} + 0.5	V
I _{IO}	Switch Continuous Current (D+, D–, Dpx, Dnx)		±300	mA
I _{IO_PK}	(Pulsed 1 ms, 10% Duty Cycle, Max).		±500	mA
PD	Power Dissipation in Still Air		800	mW
Τ _s	Storage Temperature		–65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 seconds		260	°C
ТJ	Junction Bias Under Bias		150	°C
θ_{JA}	Thermal Resistance		80	°C/W
Τ _s	Storage Temperature		-65 to +150	°C
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating Oxygen	Index: 30% – 35%	UL94–V0 (0.125 in)	°C
ESD	ESD Protection H	uman Body Model Machine Model	3000 200	V
١L	Latch-up Current, Above V _{CC} and below GND at 125°C	(Note 1)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{DD}	Positive DC Supply Voltage	3.0	3.6	V
V _S	Switch Input / Output Voltage (D+, D–, Dpx, Dnx)	-2.9	V _{DD}	V
V _{IN}	Digital Select Input Voltage (EN, SEL)	GND	V _{DD}	V
T _A	Operating Temperature Range	-40	+85	°C

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): $V_{DD} = +3.0$ V to +3.6 V, GND = 0 V, $V_S = 2$ V_{RMS}, $R_{LOAD} = 20$ k Ω , f = 1 kHz, $V_{SELH} = V_{ENH} = 1.4$ V, $V_{SELL} = V_{ENL} = 0.5$ V, (Note 2), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
ANALOG SWITCH CHARA	ACTERISTICS						
Analog Signal Range, V _{ANALOG}		3.3	Full	-	2	-	V _{RMS}
$ \begin{array}{l} \text{ON-Resistance, } r_{\text{ON}} \\ \text{I}_{\text{D+}} \text{ or } I_{\text{D-}} = 80\text{mA}, \ \text{V}_{\text{Dpx}} \text{ or } \text{V}_{\text{Dnx}} = \\ -2.828 \ \text{V} \text{ to } +2.828 \ \text{V} \text{ (See Figure 5)} \end{array} $	3.3	25	-	2.1	-	Ω	
		Full	-	2.5	-		
r _{ON} Matching Between	I_{D+} or I_{D-} = 80mA, V_{Dpx} or V_{Dnx} = Voltage at max r_{ON} over -2.828 V	3.3	25	-	0.046	-	Ω
$ \begin{array}{llllllllllllllllllllllllllllllllllll$		Full	-	0.23	-		
r _{ON} Flatness, r _{FLAT(ON)}	Flatness, $r_{FLAT(ON)}$ I_{D_+} or $I_{D} = 80mA$, V_{Dpx} or $V_{Dnx} = 100000000000000000000000000000000000$	3.3	25	-	0.047	0.05	Ω
	–2.828 V, 0V, +2.828 V (Note 5)		Full	-	0.092	-	

2. V_{IN} = input voltage to perform proper function.

3. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

 Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

6. Limits established by characterization and are not production tested.

7. r_{ON} matching between channels is calculated by subtracting the channel with the highest max r_{ON} value from the channel with lowest max r_{ON} value.

8. Crosstalk is inversely proportional to source impedance.

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): V _{DD} = +3.0 V to +3.6 V, GND = 0 V, V _S = 2 V _{RMS} , R _{LOAD} =
$20 \text{ k}\Omega$, f = 1 kHz, V _{SELH} = V _{ENH} = 1.4 V, V _{SELL} = V _{ENL} = 0.5 V, (Note 2), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
ANALOG SWITCH CHARAC	TERISTICS						
D+, D–, Dpx, Dnx Pull– down Resistance	V_{Dpx} or $V_{Dnx} = -2.83$ V, 2.83 V, $V_{D_{+}}$ or $V_{D_{-}} = -2.83$ V, 2.83 V,	3.6	25	225	300	375	kΩ
	V _{EN} = 3.6 V, measure current, calculate resistance.		Full	-	345	-	
DYNAMIC CHARACTERIST	CS						
THD+N	V_S = 2 $V_{RMS},$ f = 1 kHz, A–weighted filter, R_{LOAD} = 20 $k\Omega$	3.3	25	-	< -116	-	dB
	V_S = 1.9 V_{RMS} , f = 1 kHz, A–weight- ed filter, R _{LOAD} = 20 k Ω		25	-	< -116	-	
	V_S = 1.8 V_{RMS} , f = 1 kHz, A–weight- ed filter, R_{LOAD} = 20 k Ω		25	-	< -116	-	
	$V_S = 0.707 V_{RMS}$, f = 1 kHz, A–weighted filter, R _{LOAD} = 32 Ω		25	-	< -112	-	
SNR	f = 20 Hz to 20 kHz, A–weighted filter, inputs grounded, R_{LOAD} = 20 kΩ or 32 Ω	3.3	25	-	> 125	-	dBV
Insertion Loss, G _{ON}	f = 1 kHz, R_{LOAD} = 20 k Ω	3.3	25	-	±0.004	-	dB
Gain vs Frequency, G _f	f = 20 Hz to 20 kHz, R_{LOAD} = 20 kΩ, reference to G_{ON} at 1 kHz	3.3	25	-	±0.0008	-	dB
Stereo Channel Imbalance Dp0 and Dn0, Dp1 and Dn1	f = 20 Hz to 20 kHz, R_{LOAD} = 20 k Ω	3.3	25	-	±0.0001	-	dB
OFF–Isolation (Disabling)	f = 20 Hz to 22 kHz, D+ = D- = 2 V _{RMS} , R _{LOAD} = 20 kΩ, = 3.3 V, SEL = "X"	3.3	25	-	112	-	dB
	f = 20 Hz to 22 kHz, V _{D+} or V _{D-} = 0.7 V _{RMS} , R _{LOAD} = 32 Ω		25	-	129	-	
Crosstalk (Channel-to- Channel)	$\begin{array}{l} R_L = 20 \; k\Omega, f = 20 \; Hz \; to \; 20 \; kHz, \\ V_S = 2 \; V_{RMS}, \; signal \; source \; imped- \\ ance = 20 \; \Omega, \; (Note \; 8) \end{array}$	3.3	25	-	102	-	dB
	$ \begin{array}{l} R_{L} = 32 \; \Omega, f = 20 \; Hz \; to \; 20 \; kHz, V_{S} \\ = 0.7 \; V_{RMS}, signal \; source \; imped- \\ ance = 20 \; \Omega, (Note \; 8) \end{array} $		25	-	129	-	
PSRR	f = 1 kHz, V _S = 100 mV _{RMS} , inputs grounded	3.3	25	-	131	-	dB
	f = 20 kHz, V _S = 100 mV _{RMS} , in- puts grounded		25	-	133	-	
Bandwidth, -3 dB	$R_{LOAD} = 50 \ \Omega$	3.3	25	-	580	-	MHz
ON to Disable Time, T _{TRANS-OM}		3.3	25	-	250	-	ns
Disable to ON Time, T _{TRANS-MO}	V _{IS} = 1.5 V	3.3	25	-	1680	-	μs
Turn–ON Time, t _{ON}		3.3	25	-	14	-	μS
Turn–OFF Time, t _{OFF}	V_{Dpx} or V_{Dnx} = 1.5 V, V_{EN} = 0 V, R _L = 32 Ω (See Figure 2)	3.3	25	-	95	-	ns

V_{IN} = input voltage to perform proper function.
 The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
 Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by charac-

terization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

 Limits established by characterization and are not production tested.
 r_{ON} matching between channels is calculated by subtracting the channel with the highest max r_{ON} value from the channel with lowest max r_{ON} value.
8. Crosstalk is inversely proportional to source impedance.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 3, 4)	Тур	Max (Notes 3, 4)	Units
DYNAMIC CHARACTERIST			. ,	(, , , , , , , , , , , , , , , , , , ,	-76	(, , , , , , , , , , , , , , , , , , ,	
Break–Before–Make Time Delay, t _D		3.6	25	-	10	-	μs
OFF-Isolation	$ \begin{array}{l} R_{L} = 50 \ \Omega, \ f = 1 \ MHz, \ V_{D+} \\ or \ V_{D-} = 1 \ V_{RMS} \ (See \ Figure 4) \end{array} $	3.3	25	-	70	-	dB
Crosstalk (Channel-to-Channel)	$\begin{array}{l} R_{L} = 50 \ \Omega, \ f = 1 \ MHz, \ V_{D+} \ or \\ V_{D-} = 1 \ V_{RMS} \ (See \ Figure 4) \end{array}$	3.3	25	-	89	-	dB
Lx, Rx OFF Capacitance, C _{OFF}	$ f = 1 \text{ MHz}, V_{Dpx} \text{ or } V_{Dnx} = V_{D+} $ or $V_{D-} = 0 \text{ V}$ (See Figure 7)	3.3	25	-	2.7	-	pF
L, R ON Capacitance, $C_{COM(ON)}$	$ f = 1 \text{ MHz}, V_{Dpx} \text{ or } V_{Dnx} = \\ V_{COM} = 0 \text{ V} (See Figure 7) $	3.3	25	-	8.9	-	pF
Differential Insertion	f = 10 MHz	3.3	25	-	-0.22	-	dB
Loss, D _{IL}	f = 800 MHz	3.3	25	-	-3.3	-	
Differential OFF-	f = 10 MHz	3.3	25	-	-44	-	dB
Isolation, D _{ISO}	f = 800 MHz	3.3	25	-	-16	-	
Differential	f = 10 MHz	3.3	25	-	-44	-	dB
Crosstalk, D _{CTK}	f = 800 MHz	3.3	25	-	–16	-	

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND): V _{DD} = +3.0 V to +3.6 V, GND = 0 V, V _S = 2 V _{RMS} , R _{LOAD} =
20 k Ω , f = 1 kHz, V _{SELH} = V _{ENH} = 1.4 V, V _{SELL} = V _{ENL} = 0.5 V, (Note 2), Unless otherwise specified.

POWER SUPPLY CHARACTERISTICS

Power Supply Range, V _{DD}		3.3	Full	3	-	3.6	V
Positive Supply	$V_{EN} = 0 V$, $V_{SEL} = 0 V$ or V_{DD}	3.6	25	-	54	65	μA
Current, I+			Full	-	59	-	
	$V_{EN} = V_{DD}, V_{SEL} = 0 V \text{ or } V_{DD}$	3.6	25	-	14	40	μA
			Full	-	15	-	
	V _{EN} = 0 V, V _{SEL} = 1.8 V	3.6	25	-	55	65	μA
			Full	-	58	-	

2. V_{IN} = input voltage to perform proper function.

 The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
 Parameters with MIN and/or MAX limits are 100% tested at +25°C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

5. Flatness is defined as the difference between maximum and minimum value of ON-resistance at the specified analog signal voltage points.

6. Limits established by characterization and are not production tested.

7. rON matching between channels is calculated by subtracting the channel with the highest max rON value from the channel with lowest max r_{ON} value.

8. Crosstalk is inversely proportional to source impedance.

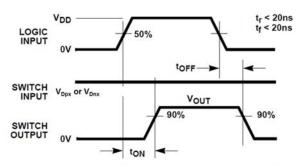
DC ELECTRICAL CHARACTERISTICS – Digital Section (Voltages referenced to GND): V_{DD} = +3.0 V to +3.6 V, GND = 0 V, V_S = 2 V_{RMS} , R_{LOAD} = 20 k Ω , f = 1 kHz, V_{SELH} = V_{ENH} = 1.4 V, V_{SELL} = V_{ENL} = 0.5 V, (Note 9), Unless otherwise specified.

Parameter	Test Conditions	Supply (V)	Temp (°C)	Min (Notes 10, 11)	Тур	Max (Notes 10, 11)	Units
DIGITAL INPUT CHARACT	ERISTICS						
Input Voltage Low, V _{SELL} , V _{ENL}		3.3	Full	-	-	0.5	V
Input Voltage High, V _{SELH} , V _{ENH}		3.3	Full	1.4	-	-	V
Input Current, I _{SELH} , I _{SELL}	V_{EN} = 0 V, V_{SEL} = 0 V or V_{DD}	3.6	Full	-0.5	0.01	0.5	μA
Input Current, I _{ENL}	$V_{SEL} = V_{DD}, V_{EN} = 0 V$	3.6	Full	-1.3	-0.7	0.3	μA
Input Current, I _{ENH}	V_{SEL} = 0 V, V_{EN} = V_{DD}	3.6	Full	-0.5	0.01	0.5	μA

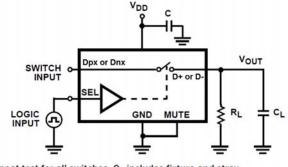
9. V_{IN} = input voltage to perform proper function.

10. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet. 11. Parameters with MIN and/or MAX limits are 100% tested at +25^[2]C, unless otherwise specified. Temperature limits established by characterization and are not production tested.

TEST CIRCUITS AND WAVEFORMS

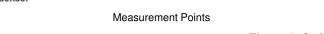


Logic input waveform is inverted for switches that have the opposite logic sense.

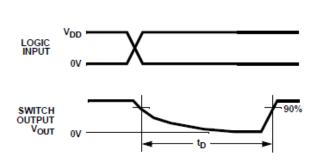


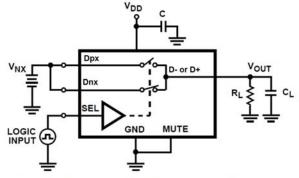
Repeat test for all switches. C_L includes fixture and stray capacitance. $V_{OUT} = V_{(Dpx \text{ or } Dnx)} \frac{R_L}{R_L + rON}$

Test Circuit







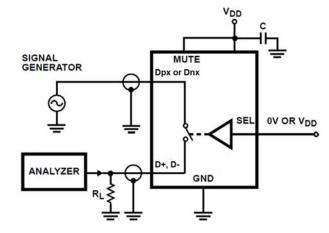


Repeat test for all switches. CL includes fixture and stray capacitance.

Measurement Points

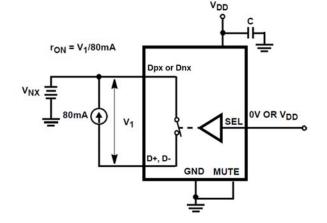
Test Circuit





Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

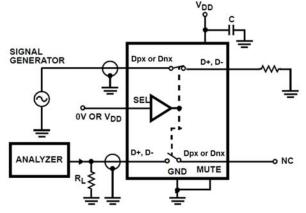
Figure 4. Off-Isolation Test Circuit



Repeat test for all switches.

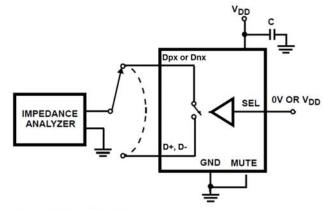


TEST CIRCUITS AND WAVEFORMS



Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

Figure 6. Crosstalk Test Circuit



Repeat test for all switches.

Figure 7. Capacitance Test Circuit

TYPICAL PERFORMANCE CURVES:

 $T_A = +25^{\circ}C$, Unless Otherwise Specified

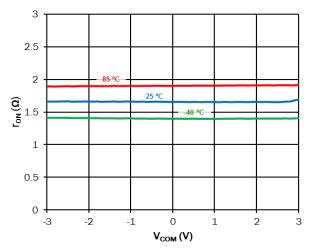
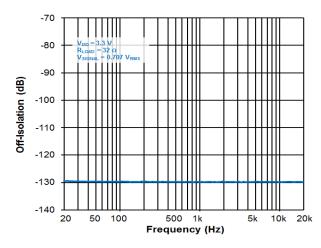
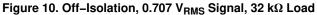


Figure 8. On-Resistance vs. Switch Voltage





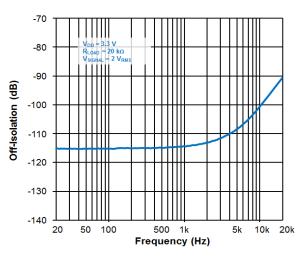
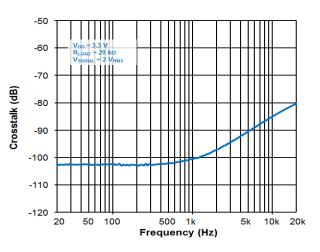
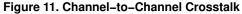


Figure 9. Off–Isolation, 2 V_{RMS} Signal, 20 k Ω Load





TYPICAL PERFORMANCE CURVES:

 $T_A = +25^{\circ}C$, Unless Otherwise Specified

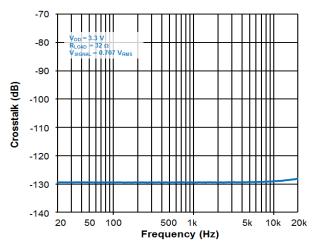
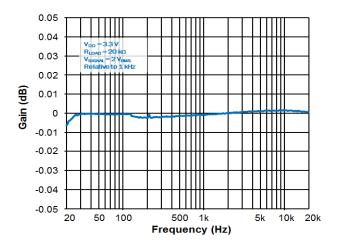
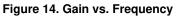


Figure 12. Channel-to-Channel Crosstalk





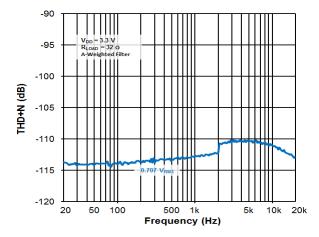


Figure 16. THD+N vs. Signal Levels vs. Frequency

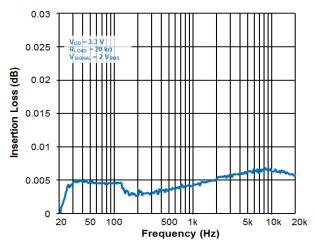


Figure 13. Insertion Loss vs. Frequency

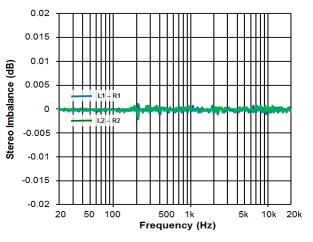


Figure 15. Stereo Imbalance vs. Frequency

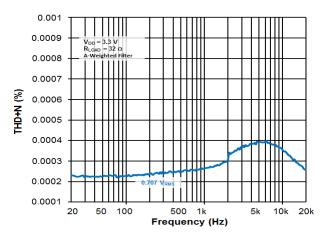


Figure 17. THD+N vs. Signal Levels vs. Frequency

TYPICAL PERFORMANCE CURVES:

 $T_A = +25^{\circ}C$, Unless Otherwise Specified

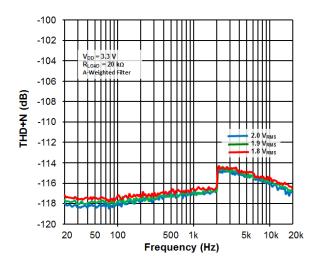


Figure 18. THD+N vs. Signal Levels vs. Frequency

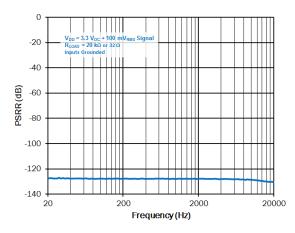


Figure 20. PSRR vs. Frequency

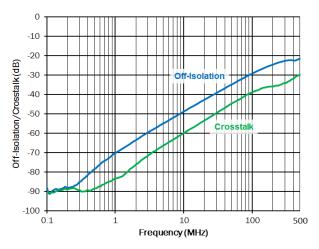


Figure 22. Crosstalk and Off–Isolation

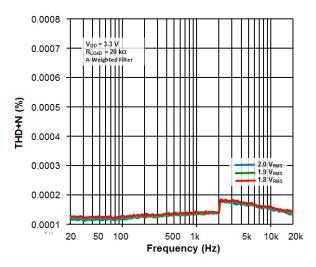


Figure 19. THD+N vs. Signal Levels vs. Frequency

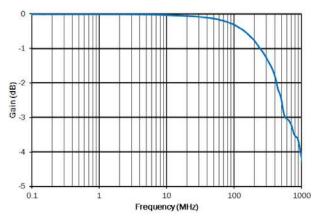


Figure 21. Frequency Response

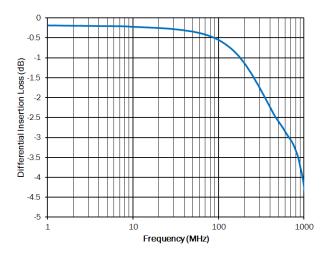


Figure 23. Differential Crosstalk

TYPICAL PERFORMANCE CURVES:

 $T_A = +25^{\circ}C$, Unless Otherwise Specified

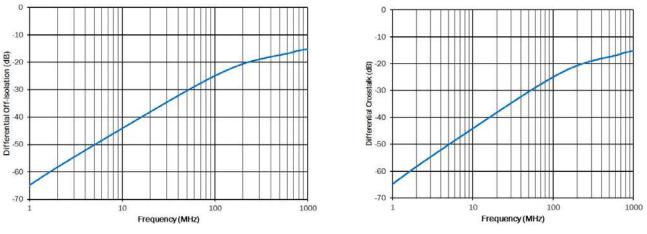


Figure 24. Differential Off–Isolation

Figure 25. Differential Crosstalk

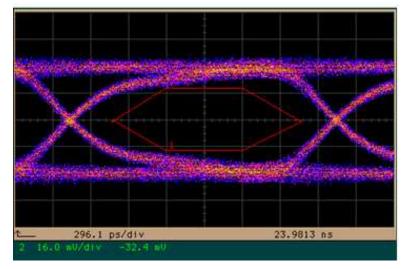
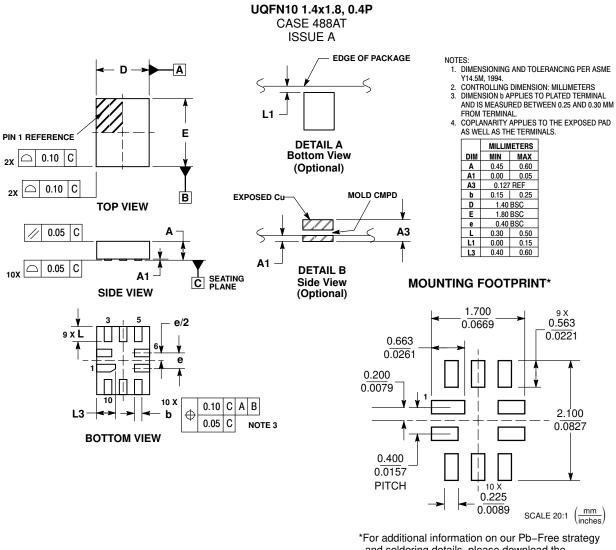


Figure 26. USB 2.0 High–Speed Eye Diagram

PACKAGE DIMENSIONS



and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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